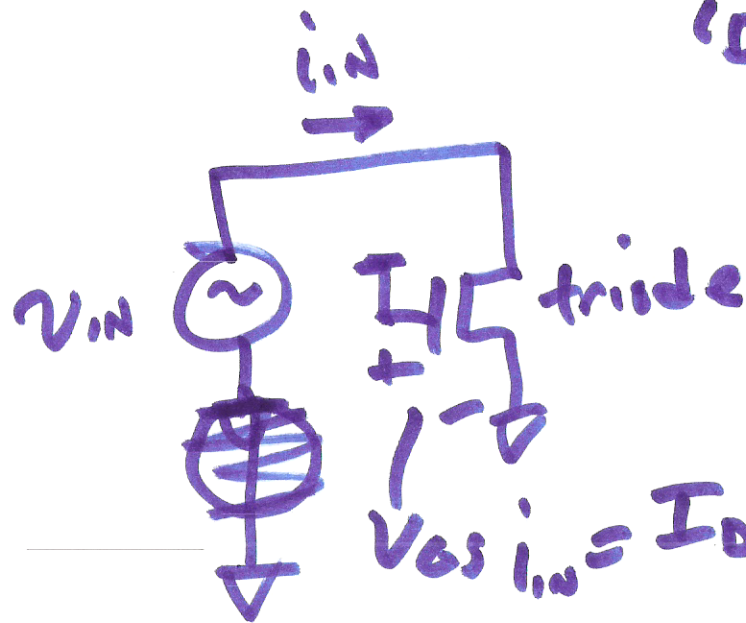




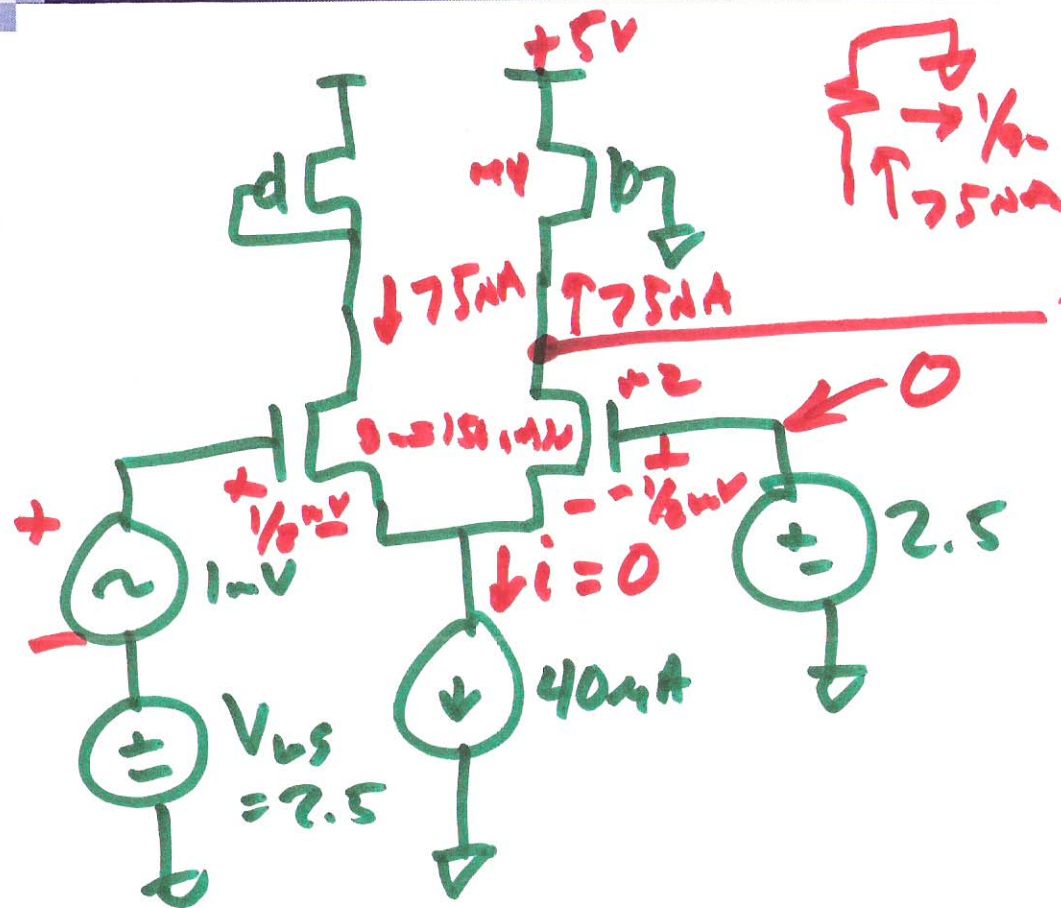
$$i_D = \beta \left( (V_{GS} - V_{THN}) v_{GS} - \frac{v_{GS}^2}{2} \right)$$

$$V_{GS} i_{in} = I_D + i_d = \beta \left( (V_{GS} - V_{THN}) v_{in} - \frac{v_{in}^2}{2} \right)$$

$$r_{in}^{-1} = \frac{\delta i_{in}}{\delta v_{in}} = \beta \left( (V_{GS} - V_{THN}) - v_{in} \right)$$

$v_{in} \ll V_{GS} - V_{THN} \neq$

$$r_{in}^{-1} \approx \beta (V_{GS} - V_{THN}) = g_m$$



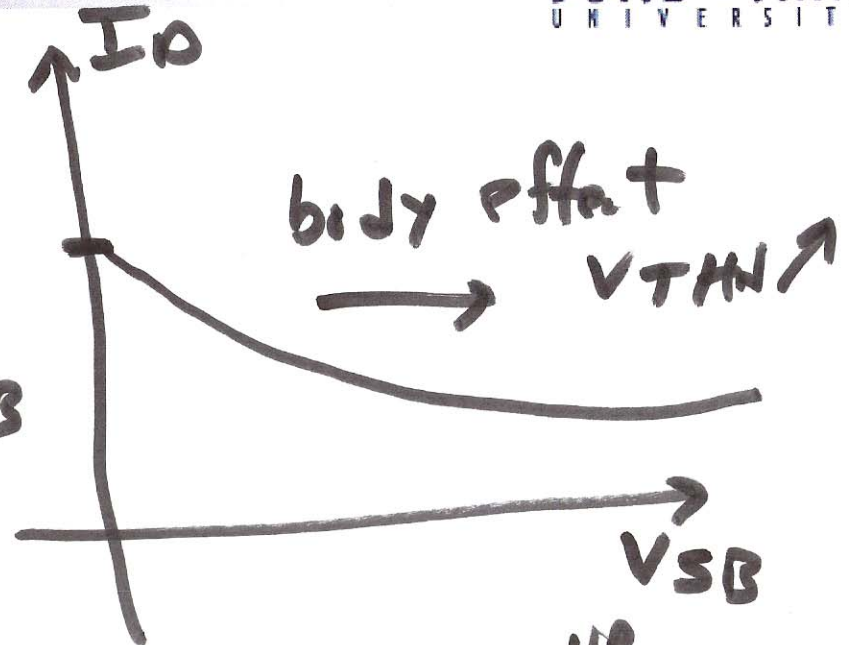
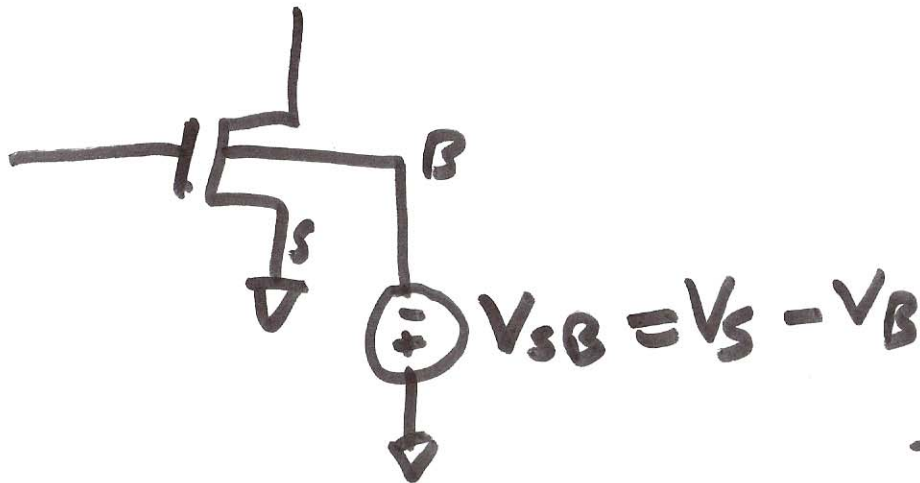
$$V_{DS} = 75nA \cdot \frac{1}{g_m}$$

$$r_{CH} = \frac{1}{40\mu A/V \cdot \frac{30}{2} (5-1)}$$

$$= 407\Omega$$

$$V_{DS} = 75n \cdot 407\Omega$$

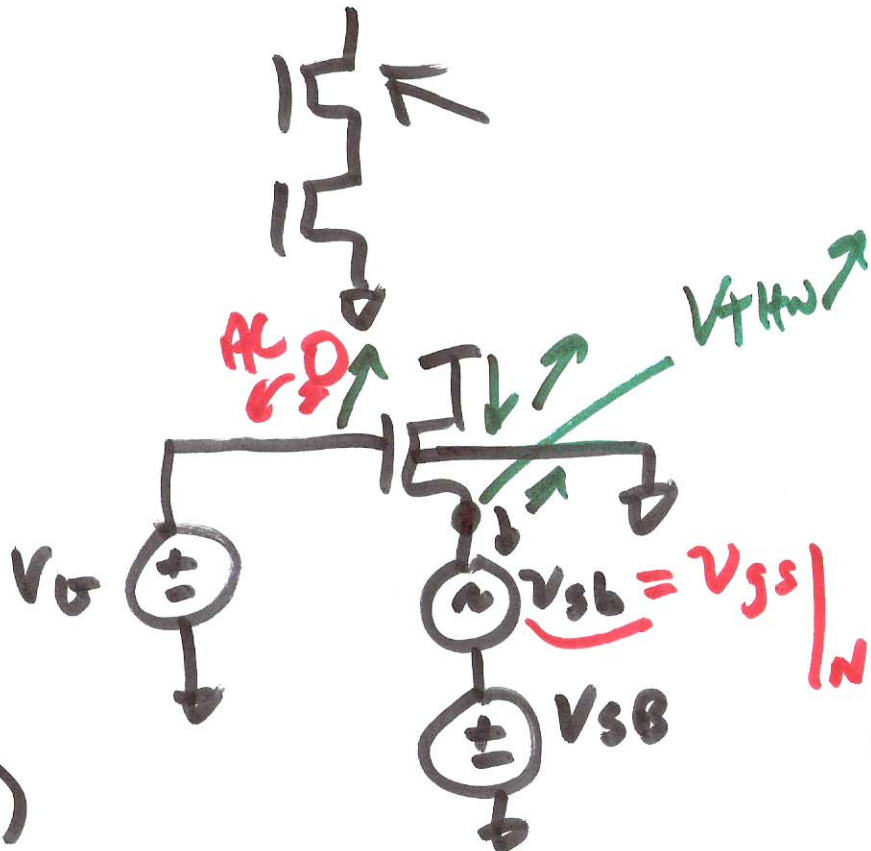
$$\approx \underline{\underline{30\mu V}}$$



$$I_D = \frac{\mu_p C_{ox}}{2} (V_{GS} - V_{THN})^2$$

$$i_D = i_{D1} + I_D = \frac{\mu_p C_{ox}}{2} (V_{GS} + V_{SB} - V_{THN})^2$$

Assume doesn't vary with  $V_{SB}$   
(yes, does give 9-)



3)



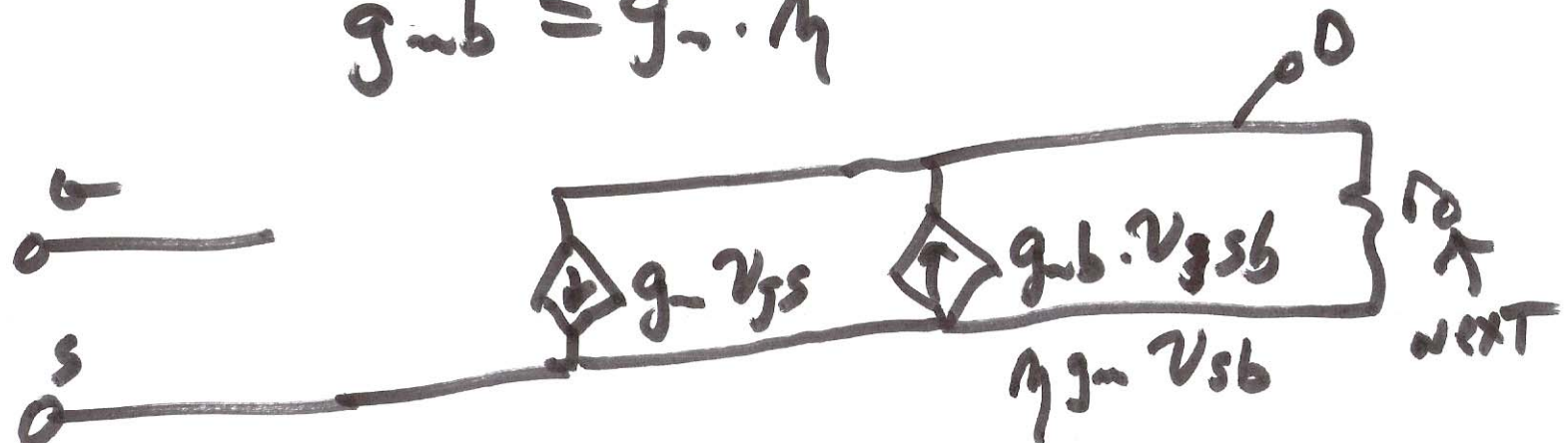
$$g_{mb} = \frac{\delta I_D + i_d}{\delta v_{sb}} = \frac{\delta \beta (V_{GS} - V_{THN})^2}{\delta v_{sb}}$$

$g_{mb}$   
↑  
body  
transconductance

$$g_{mb} = \underbrace{2\beta(V_{GS} - V_{THN})}_{g_m} \left( \underbrace{\frac{-\delta V_{THN}}{\delta v_{sb}}}_{\eta} \right)$$

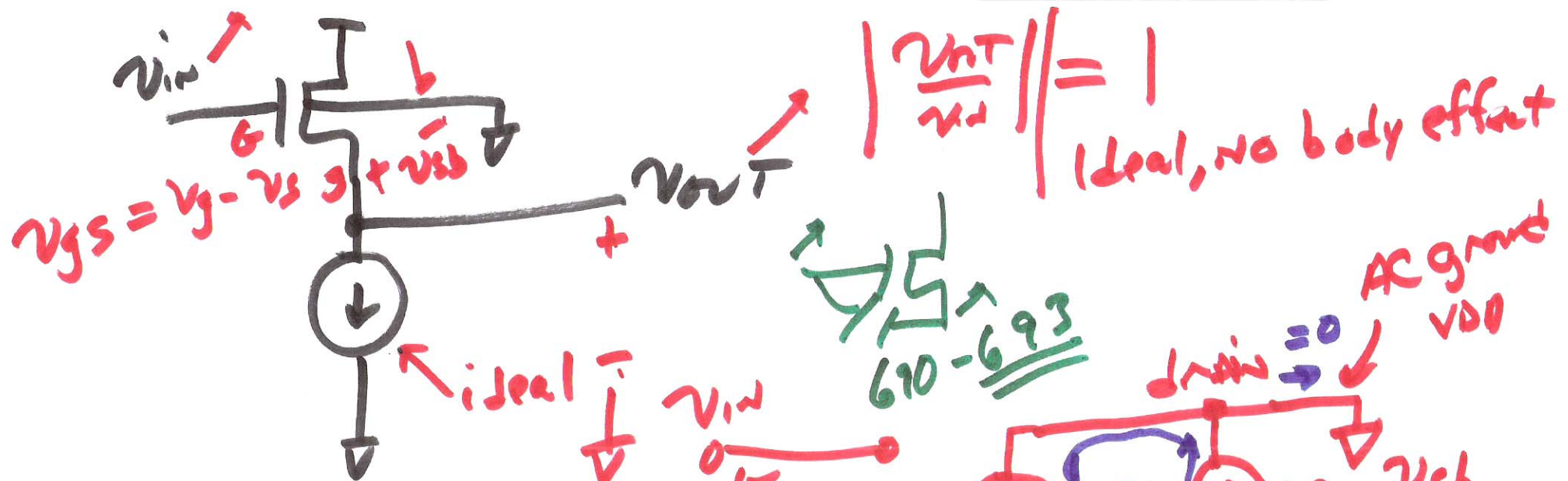
$$\eta < 1$$

$$g_{mb} = g_m \cdot \eta$$



4)

# Source followers



$$v_{sb} = v_{out}$$

$$v_{gs} = v_{in} - v_{out}$$

$$g_m v_{gs} = \mu g_m v_{sb}$$

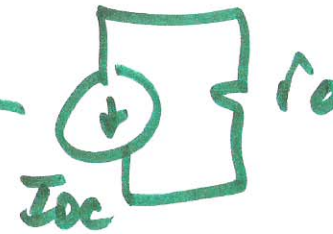
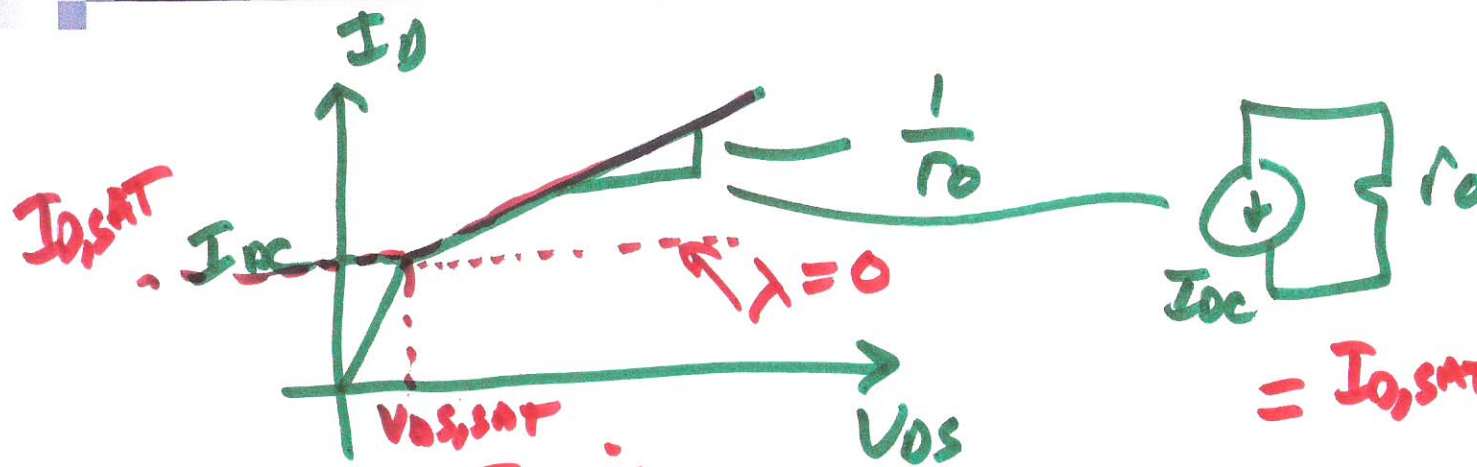
$$v_{in} - v_{out} = \mu \cdot v_{out}$$

$$\frac{v_{out}}{v_{in}} = \frac{1}{1 + \mu} < 1$$

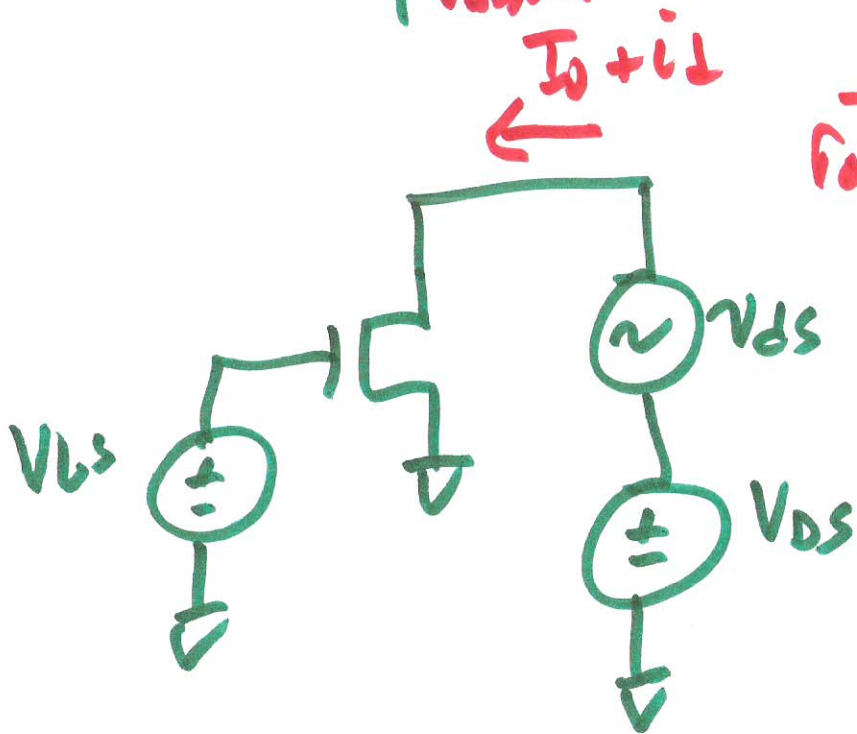
$0.1 < \mu \leq 0.4$

5)

# OUTPUT RESISTANCE



$$= I_{D,SAT} (1 + \lambda (V_{DS} - V_{DS,SAT}))$$



$$r_o^{-1} = \frac{\partial i_D}{\partial V_{DS}} \bigg|_{\substack{I_D = \text{CONST.} \\ V_{GS} = \text{CONST.}}} = \frac{\partial}{\partial V_{DS}} \left( \frac{\beta}{2} (V_{GS} - V_{TH})^2 (1 + \lambda (V_{DS} - V_{DS,SAT})) \right)$$

$$r_o^{-1} = \frac{\beta}{2} (V_{GS} - V_{TH})^2 \cdot \lambda \cdot \frac{\partial V_{DS}}{\partial V_{DS}}$$

$I_{D,SAT}$

$$r_o = \frac{1}{\lambda I_{D,SAT}}$$



$$I_D = \frac{\beta}{2} \underbrace{(V_{GS} - V_{THN})^2}_{\text{overdrive } V_{OVN}} (1 + \lambda (V_{DS} - V_{DS,SAT}))$$

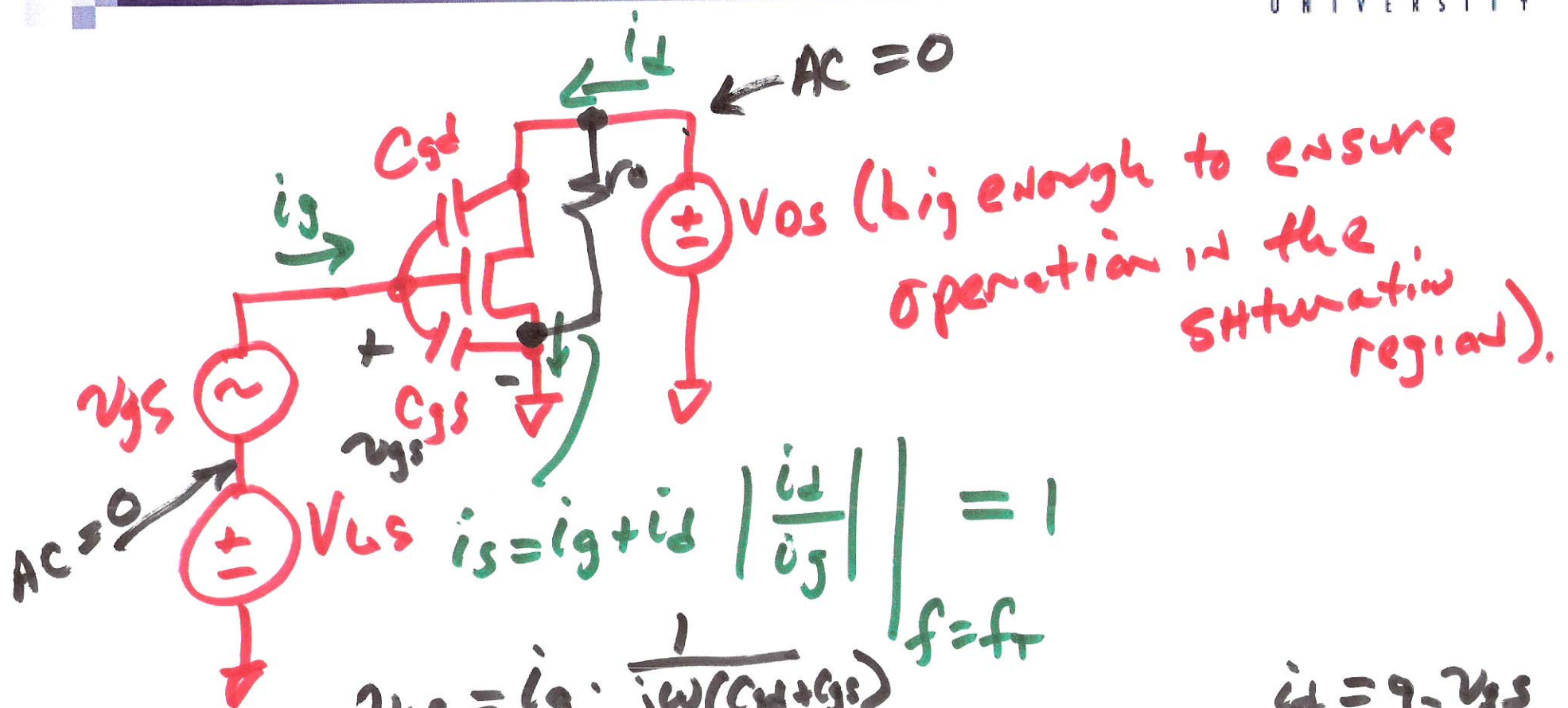
for saturation  
 $V_{GS} > V_{GS} - V_{THN}$   
 $> V_{OVN}$

Small  $V_{OVN}$   
 devices slow

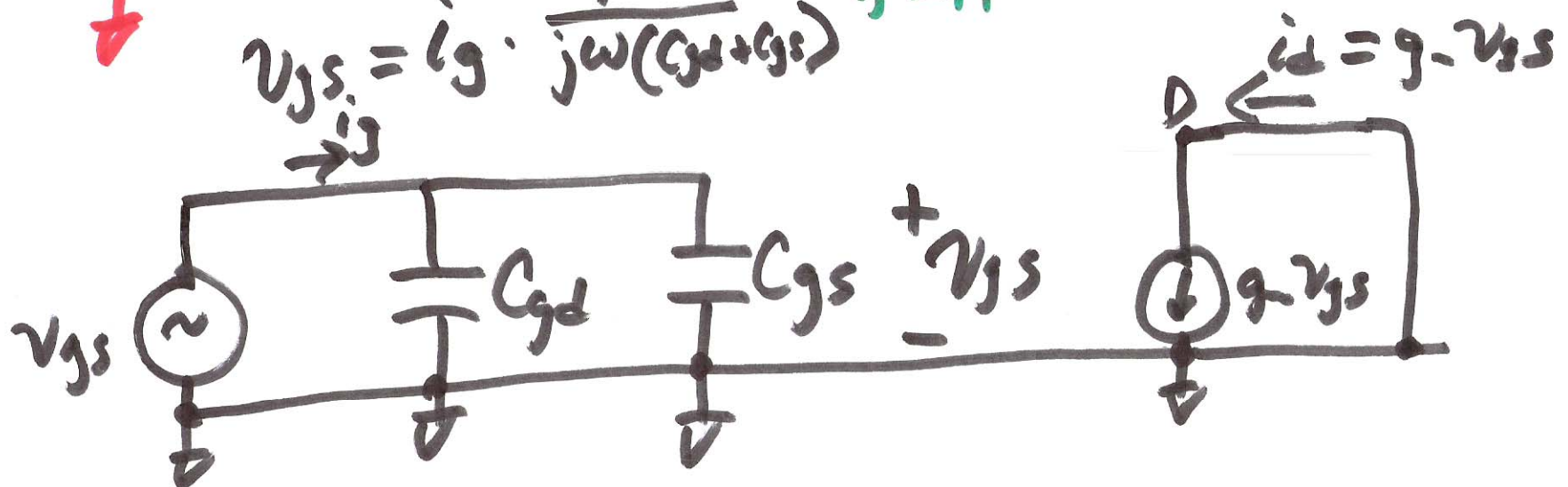
Large  $V_{OVN}$   
 devices go into  
 saturation earlier

These comments based upon  
 devices operating as  
 "square-law"

# $f_T$ - transition frequency



$$v_{gs} = i_g \cdot \frac{1}{j\omega(C_{gs} + C_{gd})}$$



8)



$$i_d = g_m \cdot \frac{v_g}{j\omega(C_{gd} + C_{gs})}$$

$$\left| \frac{i_d}{i_g} \right| = \left| \frac{g_m + j0}{1 + j\omega(C_{gd} + C_{gs})} \right|$$

$$= \frac{g_m}{2\pi f \cdot (C_{gd} + C_{gs})}$$

$$\left| \frac{i_d}{i_g} \right| = 1 = \frac{g_m}{2\pi f_T \cdot (C_{gd} + C_{gs})}$$

a)

$$f_T = \frac{g_m}{2\pi (C_{gd} + C_{gs})} \approx \frac{g_m}{2\pi C_{gs}}$$

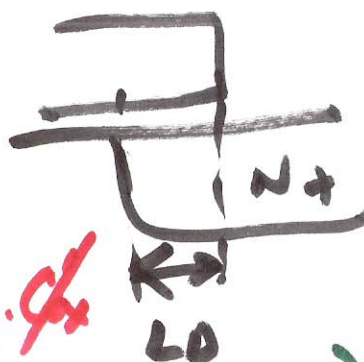
$$f_T \approx \frac{\beta(V_{GS} - V_{TH})}{2\pi C_{gs}} = \frac{\beta \cdot V_{OVN}}{2\pi C_{gs}}$$

$V_{OVN} \uparrow f_T \uparrow$

$$C_{gs} = \frac{2}{3} W L \cdot C_{ox} \quad C_{gs} \gg C_{gd}$$

$$C_{gd} = L D \cdot C_{ox}$$

← Lateral diffusion



$$f_T \approx \frac{\mu_n \cdot W (V_{GS} - V_{TH})}{2\pi L \cdot C_{gs}} =$$

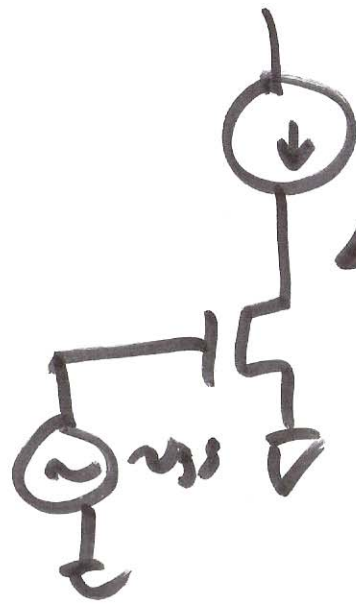
$$\frac{\mu_n \cdot C_{ox} \cdot W (V_{GS} - V_{TH})}{2\pi \cdot \frac{2}{3} L^2 C_{ox}}$$

$f_T \uparrow L \downarrow$

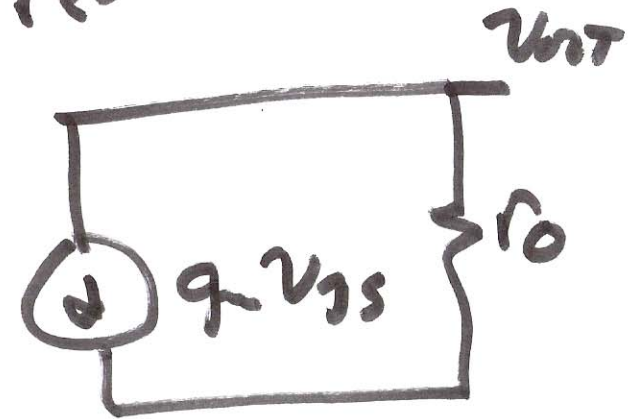
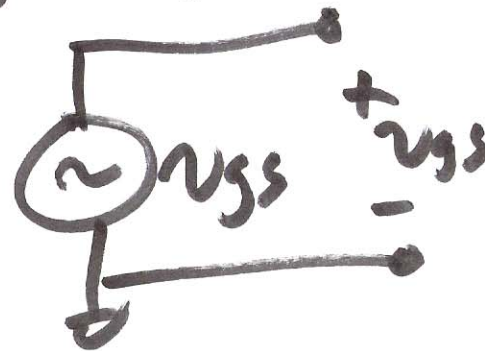
10)

$$f_T \approx \frac{\mu_n \cdot (V_{GS} - V_{TH})}{\frac{4\pi}{3} L^2}$$

# open-CKT gain



ONLY load is the MOSFET's own resistance



$$v_{out} = -g_m v_{gs} r_o$$

$$\text{open-CKT} = \left| \frac{v_{out}}{v_{in}} \right| = g_m r_o$$

$L \downarrow$   $r_o \downarrow$   $g_m \uparrow$   
see pages 300-302

$$\begin{aligned} \text{GFT} &= g_m r_o \cdot f_T \\ &= \frac{3\mu\text{N}}{2\pi L^2 \lambda} \propto \frac{\mu\text{N}}{L} \end{aligned}$$

11)